



20V P-Channel MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

| V _{DS} (V) | $R_{DS(on)}(m\Omega)$ | I _D (A) | |
|---------------------|------------------------------|--------------------|--|
| -20 | 39 @ V _{GS} = -4.5V | -4.7 | |
| | 52 @ V _{GS} = -2.5V | -4.1 | |
| | 68 @ V _{GS} = -1.8V | -2.0 | |

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- PA Switch

G S

Block Diagram

P-Channel MOSFET

Ordering Information

| Part No. | Package | Packing | | |
|---------------|---------|-----------------|--|--|
| TSM2323CX RFG | SOT-23 | 3Kpcs / 7" Reel | | |

Note: "G" denote for Green Product

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

| Parameter | Symbol | Limit | Unit | | |
|--|--------------------------|-----------------------------------|--------------|----|--|
| Drain-Source Voltage | | V _{DS} | -20 | V | |
| Gate-Source Voltage | | V_{GS} | ±8 | V | |
| Continuous Drain Current, V _{GS} @ 4.5 | V. | I _D | -4.7 | А | |
| Pulsed Drain Current, V _{GS} @ 4.5V | | I _{DM} | -20 | А | |
| Continuous Source Current (Diode Co | nduction) ^{a,b} | I _S | -1.0 | А | |
| Maximum Power Dissipation | Ta = 25°C | | 1.25 | W | |
| | Ta = 70°C | $ P_{D}$ | 0.8 | | |
| Operating Junction Temperature | | TJ | +150 | °C | |
| Operating Junction and Storage Temperature Range | | T _J , T _{STG} | - 55 to +150 | °C | |

Thermal Performance

| Parameter | Symbol | Limit | Unit |
|--|------------------|-------|------|
| Junction to Case Thermal Resistance | R⊖ _{JC} | 75 | °C/W |
| Junction to Ambient Thermal Resistance (PCB mounted) | RΘ _{JA} | 120 | °C/W |

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature





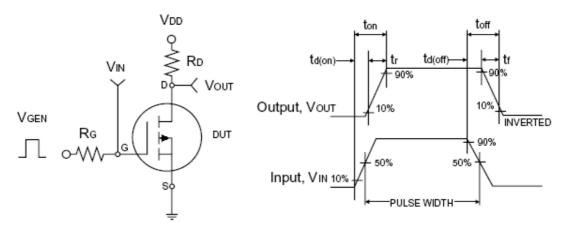


Electrical Specifications

| Parameter | Conditions | Symbol | Min | Тур | Max | Unit |
|----------------------------------|--|---------------------|------|-------|------|------|
| Static | | | | • | | |
| Drain-Source Breakdown Voltage | $V_{GS} = 0V, I_D = -250uA$ | BV _{DSS} | -20 | | | V |
| Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = -250uA$ | $V_{GS(TH)}$ | -0.4 | | -1.0 | V |
| Zero Gate Voltage Drain Current | $V_{DS} = -16V, V_{GS} = 0V$ | I _{DSS} | 1 | | -1.0 | uA |
| Gate Body Leakage | $V_{GS} = \pm 8V, V_{DS} = 0V$ | I _{GSS} | 1 | | ±100 | nA |
| On-State Drain Current | V _{DS} ≤-5V, V _{GS} = -4.5V | I _{D(ON)} | -20 | | | Α |
| | $V_{GS} = -4.5V$, $I_D = -4.7A$ | | 1 | 31 | 39 | mΩ |
| Drain-Source On-State Resistance | $V_{GS} = -2.5V$, $I_D = -4.1A$ | R _{DS(ON)} | 1 | 41 | 52 | |
| | $V_{GS} = -1.8V$, $I_D = -2.0A$ | | 1 | 54 | 68 | |
| Forward Transconductance | $V_{DS} = -5V, I_{D} = -4.7A$ | g _{fs} | 1 | 16 | | S |
| Diode Forward Voltage | $I_S = -1.0A, V_{GS} = 0V$ | V_{SD} | | - 0.7 | -1.2 | V |
| Dynamic ^b | | | | _ | | |
| Total Gate Charge | $V_{DS} = -10V, I_D = -4.7A,$ | Q_{g} | | 12.5 | 19 | |
| Gate-Source Charge | $V_{DS} = -10V, I_D = -4.7A,$ $V_{GS} = -4.5V$ | Q_gs | | 1.7 | | nC |
| Gate-Drain Charge | $V_{GS} = -4.5V$ | Q_{gd} | | 3.3 | | |
| Input Capacitance | $V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz | C _{iss} | | 1020 | | |
| Output Capacitance | | C _{oss} | | 191 | | pF |
| Reverse Transfer Capacitance | | C_{rss} | 1 | 140 | | |
| Switching ^{b,C} | | | | | | |
| Turn-On Delay Time | $V_{DD} = -10V, R_L = 10\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$ | t _{d(on)} | 1 | 25 | 40 | |
| Turn-On Rise Time | | t _r | | 43 | 65 | 20 |
| Turn-Off Delay Time | | t _{d(off)} | | 71 | 110 | nS |
| Turn-Off Fall Time | | t _f | | 48 | 75 | |

Notes:

- a. pulse test: PW ≤ 300µS, duty cycle ≤ 2%
- b. Guaranteed by design of component.
- c. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

Version: F15

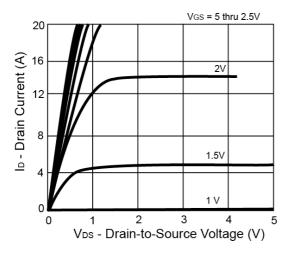




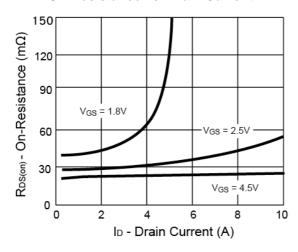


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

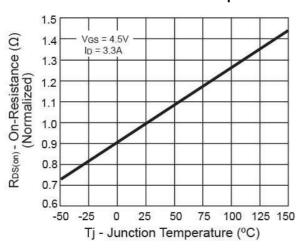
Output Characteristics



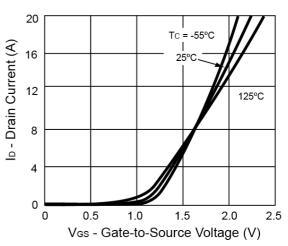
On-Resistance vs. Drain Current



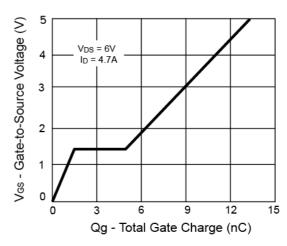
On-Resistance vs. Junction Temperature



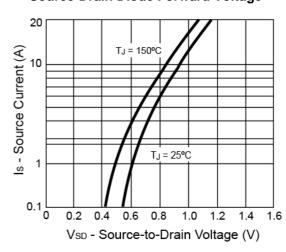
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



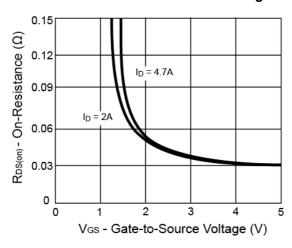




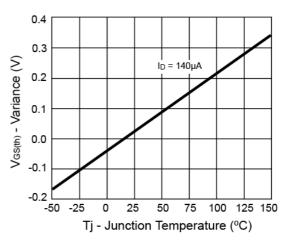


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

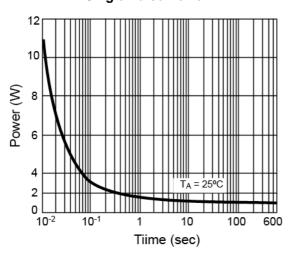
On-Resistance vs. Gate-Source Voltage



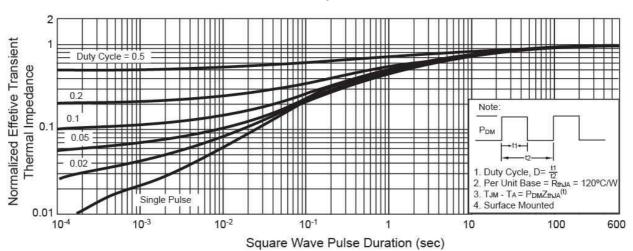
Threshold Voltage



Single Pulse Power



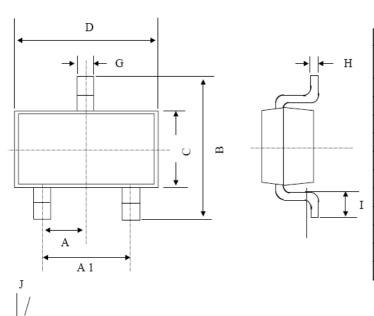
Normalized Thermal Transient Impedance, Junction-to-Ambient







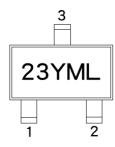
SOT-23 Mechanical Drawing



 $\bigvee_{\blacktriangledown} F$

| SOT-23 DIMENSION | | | | | | |
|------------------|----------|-------------|-----------|--------|--|--|
| DIM | MILLIM | MILLIMETERS | | INCHES | | |
| DIIVI | MIN | MAX | MIN | MAX. | | |
| Α | 0.95 BSC | | 0.037 BSC | | | |
| A1 | 1.9 | 1.9 BSC | | BSC | | |
| В | 2.60 | 3.00 | 0.102 | 0.118 | | |
| С | 1.40 | 1.70 | 0.055 | 0.067 | | |
| D | 2.80 | 3.10 | 0.110 | 0.122 | | |
| Е | 1.00 | 1.30 | 0.039 | 0.051 | | |
| F | 0.00 | 0.10 | 0.000 | 0.004 | | |
| G | 0.35 | 0.50 | 0.014 | 0.020 | | |
| Н | 0.10 | 0.20 | 0.004 | 0.008 | | |
| İ | 0.30 | 0.60 | 0.012 | 0.024 | | |
| J | 5° | 10° | 5° | 10° | | |

Marking Diagram



23 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug

W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSM2323 20V P-Channel MOSFET

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